

# 2SC1162

Silicon NPN Epitaxial

# HITACHI

## Application

Low frequency power amplifier complementary pair with 2SA715

## Outline

TO-126 MOD



1. Emitter  
2. Collector  
3. Base

## Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	Ratings	Unit
Collector to base voltage	$V_{CBO}$	35	V
Collector to emitter voltage	$V_{CEO}$	35	V
Emitter to base voltage	$V_{EBO}$	5	V
Collector current	$I_C$	2.5	A
Collector peak current	$I_{C(peak)}$	3	A
Collector power dissipation	$P_C$	0.75	W
	$P_C^{*1}$	10	W
Junction temperature	$T_j$	150	°C
Storage temperature	$T_{stg}$	-55 to +150	°C

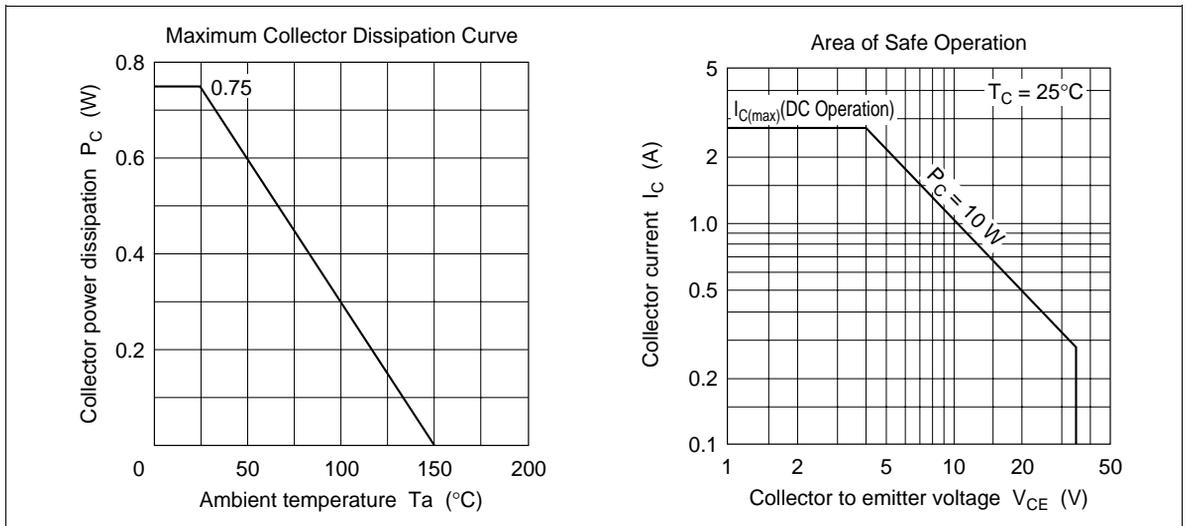
Note: 1. Value at  $T_C = 25^\circ\text{C}$ .

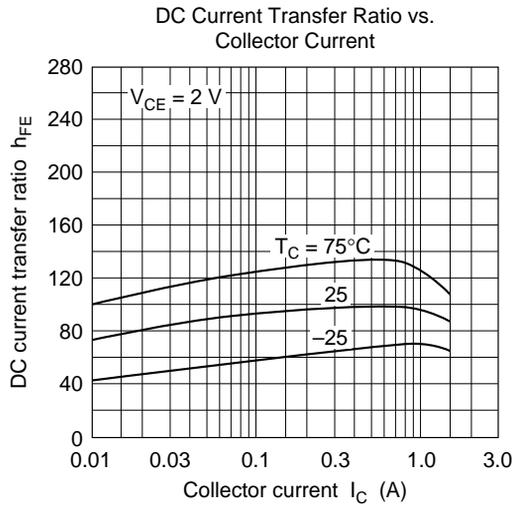
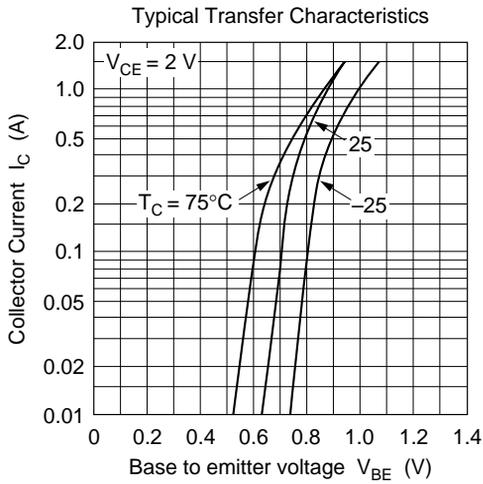
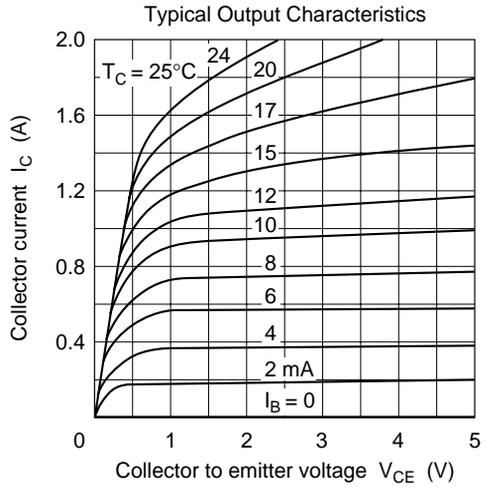
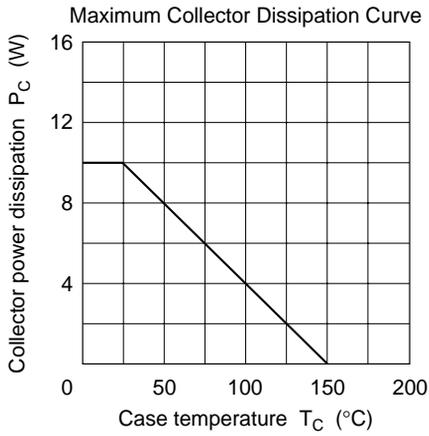
**Electrical Characteristics** ( $T_a = 25^\circ\text{C}$ )

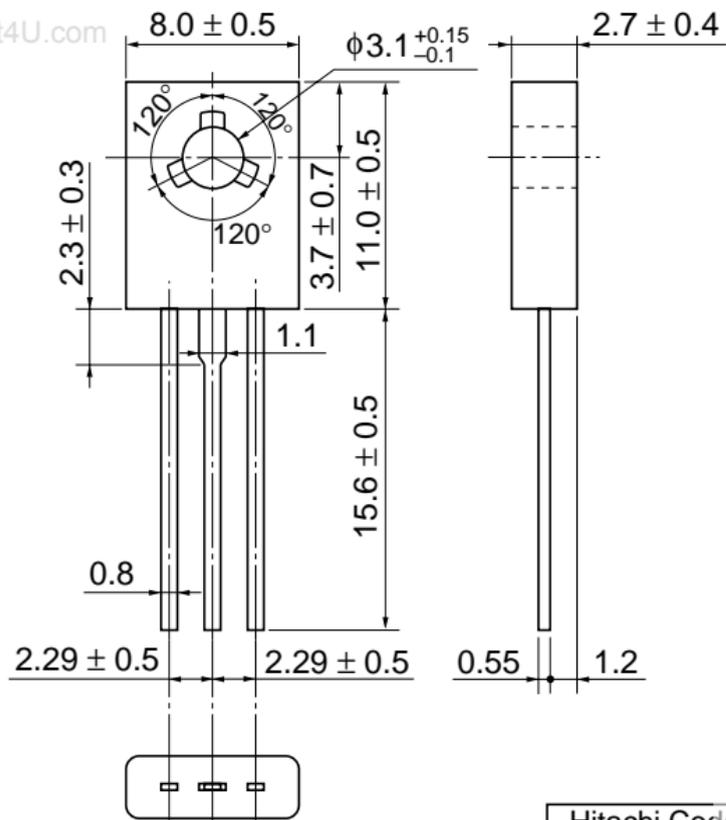
Item	Symbol	Min	Typ	Max	Unit	Test conditions
Collector to base breakdown voltage	$V_{(BR)CBO}$	35	—	—	V	$I_C = 1\text{ mA}, I_E = 0$
Collector to emitter breakdown voltage	$V_{(BR)CEO}$	35	—	—	V	$I_C = 10\text{ mA}, R_{BE} = \infty$
Emitter to base breakdown voltage	$V_{(BR)EBO}$	5	—	—	V	$I_E = 1\text{ mA}, I_C = 0$
Collector cutoff current	$I_{CBO}$	—	—	20	$\mu\text{A}$	$V_{CB} = 35\text{ V}, I_E = 0$
DC current transfer ratio	$h_{FE}^{*1}$	60	—	320		$V_{CE} = 2\text{ V}, I_C = 0.5\text{ A}$
	$h_{FE}$	20	—	—		$V_{CE} = 2\text{ V}, I_C = 1.5\text{ A}$ (pulse test)
Base to emitter voltage	$V_{BE}$	—	0.93	1.5	V	$V_{CE} = 2\text{ V}, I_C = 1.5\text{ A}$ (pulse test)
Collector to emitter saturation voltage	$V_{CE(sat)}$	—	0.5	1.0	V	$I_C = 2\text{ A}, I_B = 0.2\text{ A}$ (pulse test)
Gain bandwidth product	$f_T$	—	180	—	MHz	$V_{CE} = 2\text{ V}, I_C = 0.2\text{ A}$

Note: 1. The 2SC1162 is grouped by  $h_{FE}$  as follows.

B	C	D
60 to 120	100 to 200	160 to 320







Hitachi Code	www.DataSheet4U.com TO-18 Mod
JEDEC	—
EIAJ	—
Weight (reference value)	0.67 g

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# HITACHI

## Hitachi, Ltd.

Semiconductor & Integrated Circuits.  
Nippon Bldg., 2-6-2, Ohte-machi, Chiyoda-ku, Tokyo 100-0004, Japan  
Tel: Tokyo (03) 3270-2111 Fax: (03) 3270-5109

URL North America : <http://semiconductor.hitachi.com/>  
Europe : <http://www.hitachi-eu.com/hel/ecg>  
Asia (Singapore) : <http://www.has.hitachi.com.sg/grp3/sicd/index.htm>  
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### For further information write to:

Hitachi Semiconductor  
(America) Inc.  
179 East Tasman Drive,  
San Jose, CA 95134  
Tel: <1> (408) 433-1990  
Fax: <1> (408) 433-0223

Hitachi Europe GmbH  
Electronic components Group  
Dornacher Straße 3  
D-85622 Feldkirchen, Munich  
Germany  
Tel: <49> (89) 9 9180-0  
Fax: <49> (89) 9 29 30 00

Hitachi Europe Ltd.  
Electronic Components Group.  
Whitebrook Park  
Lower Cookham Road  
Maidenhead  
Berkshire SL6 8YA, United Kingdom  
Tel: <44> (1628) 585000  
Fax: <44> (1628) 778322

Hitachi Asia Pte. Ltd.  
16 Collyer Quay #20-00  
Hitachi Tower  
Singapore 049318  
Tel: 535-2100  
Fax: 535-1533

Hitachi Asia Ltd.  
Taipei Branch Office  
3F, Hung Kuo Building, No.167,  
Tun-Hwa North Road, Taipei (105)  
Tel: <886> (2) 2718-3666  
Fax: <886> (2) 2718-8180

Hitachi Asia (Hong Kong) Ltd.  
Group III (Electronic Components)  
7/F., North Tower, World Finance Centre,  
Harbour City, Canton Road, Tsim Sha Tsui,  
Kowloon, Hong Kong  
Tel: <852> (2) 735 9218  
Fax: <852> (2) 730 0281  
Telex: 40815 HITEC HX

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